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TABLE OF CONTENTS

Negative or Zero Thermal Expansion in Silicon Dicarboimide, Si(NCN)₂	1
<i>P. Kroll, X. Yan, R. Riedel, H. Ehrenberg</i>	
Defect Selective Etching of Thick AlN Layers Grown on 6H-SiC Seeds - A Transmission Electron Microscopy Study	7
<i>L. O. Nyakiti, J. Chaudhuri, E. A. Kenik, P. Lu, J. H. Edgar</i>	
Growth and Characterization of High-Performance GaN and Al_xGa_{1-x}N Ultraviolet Avalanche Photodiodes Grown on GaN Substrates	13
<i>R. D. Dupuis, D. Yoo, J. H. Ryou, Y. Zhang, S. C. Shen, J. Limb, P. D. Yoder, A. D. Hanser, E. Preble, K. Evans</i>	
Mn- and Fe- doped GaN for Spintronic Applications	19
<i>E. Malguth, A. Hoffmann, S. Werner, M. H. Kane, I. T. Ferguson</i>	
Characterization of Spectral Emissions from Laser Irradiated Titanium	25
<i>R. K. Akarapu, P. Dua, A. Campbell, D. Scott, A. Nassar, J. Todd, S. Copley</i>	
The Effect of Composition on the Properties of Semiconducting Transition Metal Nitrides	31
<i>M. Moreno-Armenta, A. Reyes-Serrato, G. Soto</i>	
Mn Charge States in GaMnN as a Function of Mn Concentration and Co-doping	37
<i>E. Malguth, A. Hoffmann, W. Gehlhoff, M. H. Kane, I. T. Ferguson</i>	
Phase Transitions in Silicon-Carbon-Nitride Compounds	42
<i>P. Kroll, J. Gracia, R. Riedel</i>	
Aluminum Nitride Micro-Channels Grown via Metal Organic Vapor Phase Epitaxy for MEMs Applications	47
<i>L. E. Rodak, S. Kuchibhatla, P. Famouri, T. Liu, D. Korakakis</i>	
GaN Photonic Crystal-Based, Enhanced Fluorescence Biomolecule Detection System	53
<i>J. M. Dawson, J. R. Nightingale, R. P. Tompkins, X. Cao, T. H. Myers, L. A. Hornak, D. Korakakis</i>	
Nitridoaluminosilicate CaAlSiN₃ and its Derivatives - Theory and Experiment	59
<i>M. Mikami, H. Watanabe, K. Uheda, N. Kijima</i>	
Photoelectrochemical Etching of GaN Thin Films With Varying Carrier Concentrations	66
<i>J. H. Leach, U. Ozgur, H. Morkoc</i>	
Variational Calculations of Donor Binding Energy in Rectangular Wurtzite Aluminium Gallium Nitride/Gallium Nitride Quantum Wires	72
<i>C. J. Praharaj</i>	
Sublimation Growth and Defect Characterization of AlN Single Crystals	78
<i>S. Wang, B. Raghochamachar, M. Dudley, Z. Ren, J. Han, A. G. Timmerman</i>	
Contribution of Solvothermal Processes to the Synthesis of Novel Nitrides and the Development of Shaping Processes	84
<i>G. Demazeau, G. Goglio, A. Largeteau</i>	
Shock Wave Synthesis and Exploration of High-pressure Nitrides and Related Materials	94
<i>T. Sekine</i>	
Contact Characterizations of ZrN Thin Films Obtained by Reactive Sputtering	98
<i>J. Pelleg, A. Bibi, M. Sinder</i>	

Growth and Raman Spectroscopy of Single Crystal ZnGeN₂ Rods Grown from a Molten Zn/Ge Alloy	103
<i>T. J. Peshek, S. Wang, J. C. Angus, K. Kash</i>	
Green Light Emitting Diodes under Photon Modulation	110
<i>Y. Li, J. Senawiratne, Y. Xia, M. Zhu, W. Zhao, T. Detchprohm, C. M. Wetzel</i>	
Molecular Beam Epitaxy of Nonpolar Cubic Al_xGa_{1-x}N/GaN Epilayers	116
<i>D. J. As, S. Potthast, J. Schoermann, E. Tschumak, M. F. de Godoy, K. Lischka</i>	
Electron Band Structure of MnGaN	122
<i>D. Alexandrov, N. Dietz, I. Ferguson, H. Yu</i>	
Structure of Isolated Oxygen Impurity States in InN	128
<i>D. Alexandrov, S. Butcher, N. Dietz, H. Yu</i>	
Synthesis and Sintering of Aluminium Nitride Nano-particles	134
<i>Z. Han, M. Yang, H. Zhu</i>	
Non-planar Corrugated Layered Heptazine-based Carbon Nitride: The Lowest Energy Modifications of C₃N₄	140
<i>P. Kroll, J. Gracia</i>	
The Phase Boundary Between β-Si₃N₄ and γ-Si₃N₄ at Elevated Temperatures and Pressures	146
<i>A. Togo, P. Kroll</i>	
Magnetocaloric Effects of Binary Rare Earth Nitrides	152
<i>Y. Hirayama, T. Nakagawa, T. Kusunose, T. A. Yamamoto</i>	
Density Functional Calculations of the Binding Energies and Adatom Diffusion on Strained AlN (0001) and GaN (0001) Surfaces	158
<i>V. Jindal, J. Grandusky, N. Tripathi, M. Tungare, F. Shahedipour-Sandvik</i>	
Two-Dimensional Growth Mode and Reduction of Dislocation Density in Nitride Layers	165
<i>K. Pakula, J. M. Baranowski, J. Borysiuk</i>	
Development of Homoepitaxially Grown GaN Thin Film Layers on Freestanding Bulk m-plane Substrates by Metalorganic Chemical Vapor Deposition (MOCVD)	171
<i>V. Jindal, J. Grandusky, N. Tripathi, M. Tungare, F. Shahedipour-Sandvik, P. Sandvik, V. Tilak</i>	
Superluminescence in Green Emission GaInN/GaN Quantum Well Structures under Pulsed Laser Excitation	178
<i>J. Senawiratne, S. Tomasulo, T. Detchprohm, M. Zhu, Y. Li, W. Zhao, Y. Xia, Z. Zhang, P. Persans, C. Wetzel</i>	
A Role of the Built-in Piezoelectric Field in InGaN/AlGaIn/GaN Multiple Quantum Wells in the Electroreflectance Experiments	184
<i>P. Bokov, L. Avakyan, M. Badgutdinov, A. Chervyakov, S. Shirokov, A. Yunovich, E. Vasileva, F. Snegov, D. Bauman, B. Yavich</i>	
Transmission Electron Microscopy Study of Interface Region of ALN/6H-SiC	190
<i>J. Chaudhuri, L. O. Nyakiti, P. Lu, J. H. Edgar, P. Li</i>	
Structural Analysis in Low-V-defect Blue and Green GaInN/GaN Light Emitting Diodes	196
<i>M. Zhu, T. Detchprohm, Y. Xia, W. Zhao, Y. Li, J. Senawiratne, S. You, L. Liu, E. A. Preble, D. Hanser, C. Wetzel</i>	
New Metal Nitride Compounds: Can they be Synthesized at High-Pressures?	202
<i>P. Kroll</i>	
Nitride Based Schottky-Barrier Photovoltaic Devices	207
<i>B. R. Jampana, O. K. Jani, H. Yu, I. T. Ferguson, B. E. McCandless, S. S. Hegedus, R. L. Opila, C. B. Honsberg</i>	

Preparation of AlN Thin Films by Means of CVD Using Iodide Source Under Atmospheric Pressure	213
<i>H. Iwane, N. Wakiya, N. Sakamoto, T. Nakamura, H. Suzuki</i>	
Preparation of InN by Means of AP-HCVD Using In Buffer Layers	219
<i>H. Yokoo, N. Wakiya, N. Sakamoto, T. Nakamura, H. Suzuki</i>	
Author Index	